

Quantum & Nonlinear Photonics in Silicon Carbide Daniil Lukin

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NNCI Etch Symposium

April 22, 2022



Silicon Carbide



Heteroepitaxy substrate



Abrasives





Fake diamonds



Heating elements



Power electronics

• Available on a wafer scale



 Advanced semiconductor processing technology



Widmann et al., Nano Letters (2019)

• Excellent linear and nonlinear optical properties



Guidry et al., Optica (2020) 2

Optical properties of silicon carbide



- High refractive index
- Wide bandgap suitable for visible photonics
- Large second- and third-order nonlinearity
- CMOS compatible

Wilson et al., Nat. Photon. (2020)

Color centers in silicon carbide for quantum photonics





One color center comprises multiple qubits, aka a quantum register



¹²C and ²⁸Silicon don't have a nuclear spin
¹³C and ²⁹Silicon are spin 1/2



Network-based quantum computing architecture



Nickerson et al, Phys. Rev. X 2014

Two alternative cells



Low-loss photonic interconnects are critical for fault tolerance.

What are the photonic circuit requirements?

- Photonic resonators
- Low-loss passive and active components: waveguides, switches, beamsplitters
- Efficient detectors
- Tunable of elements for homogenous operation
- Scalability to thousands of nodes

Silicon photonics have proved the required level of performance is possible for classical devices.





12 inch silicon photonics wafer

Hong Hou Intel Silicon Photonics Integration

Can silicon carbide enable the same capabilities for quantum photonics?

A pattern in integrated photonics revolutions

1960's: Silicon (Si) wafers commercialized. 2000's: Silicon-on-Insulator (SOI) commercialized.

> → Silicon nanophotonics enters golden age: scalable high density photonic circuits



1990's: Lithium Niobate (LiNbO₃) wafers commercialized. 2010's: LiNbO₃-on-Insulator is commercialized.

> → LiNbO₃ nanophotonics enters golden age ultra-efficient second-order nonlinear photonics



C. Wang, Opt. Express 26, 2018

1990's: SiC wafers commercialized

...



Silicon Carbide on insulator: previous approaches



SiC-on-insulator with pristine crystal quality



Developing ultra-low-loss-photonics in SiC





 $Q = 7.8 \times 10^5$ Lukin et al., Nature Photonics (2020)

 $Q = 1.1 \times 10^{6}$ Guidry et al., Optica (2020)



Q = 5.6 x 10⁶ 0.08 dB/cm loss



CMOS- compatible processing

Guidry et al., Nature Photonics (2022)

Nonlinear optics in SiC – Second Harmonic Generation



Ring resonator optimized for second harmonic generation

Demonstration of efficient SHG in SiC resonators

Concept figure of integrating quantum emitters with on chip frequency conversion

Nonlinear optics in SiC – Soliton generation





Kiyoul Yang





Material	\mathbf{Q}_0 (M)	FSR (GHz)	Soliton operation power (OPO threshold) (mW)	Reference
Si_3N_4	260	5	~ 20	Bowers (UCSB)
${ m Si}_3{ m N}_4$	8	194	1.3(1.1)	Lipson (Columbia)
${ m Si}_3{ m N}_4$	15	99	6.2(1.7)	Kippenberg (EPFL)
$ m SiO_2/Si_3N_4$	120	15	28(5)	Vahala (Caltech)
$LiNbO_3$	2.4	199.7	5.2	Lin (Rochester)
AlGaAs	1.5	450	1.77 (0.07)	Bowers (UCSB)
SiC	5.6	350	→ 2.3 (0.51) →	Vuckovic (Stanford)

Nonlinear optics in SiC – Quantum study of solitons

1700







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Observation and theoretical modeling of quantum properties of soliton microcombs

Guidry et al., Quantum Optics of Soliton Microcombs, Nature Photonics (2022)

Photonic inverse design

Photonics optimization critical for implementation of scalable and practical systems

Stanford Photonics INverse design Software (SPINS) Vuckovic Group - Stanford OTL Docket Number: S18-012 SPINS–B (open source) on Github http://github.com/stanfordnqp/spins-b

L. Su et al, Applied Physics Reviews, Vol.7, Issue 1, DOI: 10.1063/1.5131263 (2020)





Photonic inverse design



- Photonic circuits require very high efficiencies and often novel functionalities
- Rely on sophisticated optimization techniques, but also take into account fabrication constraints

Logan Su et al, Appl. Phys. Rev. 7, 011407 (2020)

Stanford Photonics INverse design Software (SPINS) Vuckovic Group - Stanford OTL Docket Number: S18-012 **SPINS–B** (open source, 3D) on Github http://github.com/stanfordnqp/spins-b

Inverse design + SiC enables numerically-optimized nonlinear photonics







Joshua Yang



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Towards commercial waferscale SiC on insulator: photoelectrochemically



Bracher and Hu et al, APL, 2015



Magyar et al, APL, 2014



Goal: Monolithic realization of integrated quantum network in SiC



SiCOI devices in high-quality SiC epitaxy





Takeshi Ohshima

Jawad Ul-Hassan

Locating single defects in microdisk resonators

Once on resonance, scan a CW above resonant laser while collecting emission from the coupler.



diagram of the edge scattering

scattering

from edge

emitter

Edge-coupled disk resonators

scattering loss from support
< 1% in simulation</pre>



Total coupling efficiency into single-mode fiber up to 24%

view from edge view from edge, focus at waveguide end

Stable color centers in SiCOI nanophotonics



Purcell enhancement

Dipole induced transparency

Two-photon interference between two SiC color centers

Single-photon interference between two emitters in a resonator

excitation with a weak coherent resonant pulse

Toward many-emitter systems via spectral control

Frequency control of color centers

Floquet states

Lukin, White et al, npj Quantum Info (2020)

Goal: Monolithic realization of integrated quantum network in SiC

Acknowledgements

Sattwik Deb Mishra

STANFORD NANO SHARED FACILITIES **SNSF**

Jawad Ul-Hassan

Misagh Ghezellou

Nanoscale and Quantum Photonics Lab at Stanford

Stanford University